



New Product

SUM110N08-07
Vishay Siliconix

N-Channel 75-V (D-S) MOSFET

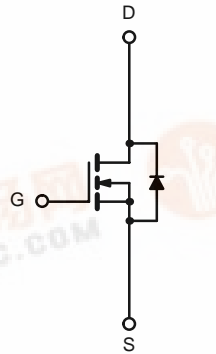
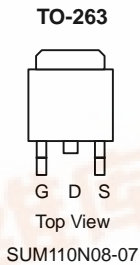
PRODUCT SUMMARY		
V _{(BR)DSS} (V)	r _{DS(on)} (Ω)	I _D (A)
75	0.007 @ V _{GS} = 10 V	110

FEATURES

- TrenchFET® Power MOSFET
- New Low Thermal Resistance Package

APPLICATIONS

- Automotive
 - Boardnet 42-V EPS and ABS
 - Motor Drives
- High Current
- DC/DC Converters



ABSOLUTE MAXIMUM RATINGS (T _C = 25°C UNLESS OTHERWISE NOTED)			
Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	75	V
Gate-Source Voltage	V _{GS}	±20	
Continuous Drain Current (T _J = 175°C)	I _D	T _C = 25°C	110
		T _C = 125°C	63
Pulsed Drain Current	I _{DM}	350	A
Avalanche Current	I _{AR}	75	
Repetitive Avalanche Energy ^a	E _{AR}	280	mJ
Maximum Power Dissipation ^a	P _D	T _C = 25°C	200 ^b
		T _A = 25°C ^d	3.7
Operating Junction and Storage Temperature Range	T _J , T _{stg}	-55 to 175	°C

THERMAL RESISTANCE RATINGS			
Parameter	Symbol	Limit	Unit
Junction-to-Ambient	R _{thJA}	40	°C/W
Junction-to-Case	R _{thJC}	0.75	

Notes:
 a. Duty cycle ≤ 1%.
 b. See SOA curve for voltage derating.
 c. When mounted on 1" square PCB (FR-4 material).



SPECIFICATIONS (T _J = 25 °C UNLESS OTHERWISE NOTED)						
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{DS} = 0 V, I _D = 250 μA	75			V
Gate-Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250 μA	2.5		4.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0 V, V _{GS} = ±20 V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60 V, V _{GS} = 0 V			1	μA
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 125 °C			50	
		V _{DS} = 60 V, V _{GS} = 0 V, T _J = 175 °C			250	
On-State Drain Current ^a	I _{D(on)}	V _{DS} ≥ 5 V, V _{GS} = 10 V	120			A
Drain-Source On-State Resistance ^a	r _{DS(on)}	V _{GS} = 10 V, I _D = 30 A		0.0055	0.007	Ω
		V _{GS} = 10 V, I _D = 30 A, T _J = 125 °C			0.013	
		V _{GS} = 10 V, I _D = 30 A, T _J = 175 °C			0.017	
Forward Transconductance ^a	g _{fs}	V _{DS} = 15 V, I _D = 30 A	30			S
Dynamic^b						
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		5250		pF
Output Capacitance	C _{oss}			700		
Reverse Transfer Capacitance	C _{rss}			310		
Total Gate Charge ^c	Q _g	V _{DS} = 35 V, V _{GS} = 10 V, I _D = 110 A		90	165	nC
Gate-Source Charge ^c	Q _{gs}			24		
Gate-Drain Charge ^c	Q _{gd}			27		
Turn-On Delay Time ^c	t _{d(on)}	V _{DD} = 35 V, R _L = 0.4 Ω I _D ≅ 85 A, V _{GEN} = 10 V, R _G = 2.5 Ω		20	30	ns
Rise Time ^c	t _r			100	150	
Turn-Off Delay Time ^c	t _{d(off)}			45	70	
Fall Time ^c	t _f			75	115	
Source-Drain Diode Ratings and Characteristics (T_C = 25 °C)^b						
Continuous Current	I _S				110	A
Pulsed Current	I _{SM}				350	
Forward Voltage ^a	V _{SD}	I _F = 110 A, V _{GS} = 0 V		1.0	1.5	V
Reverse Recovery Time	t _{rr}	I _F = 85 A, di/dt = 100 A/μs		75	120	ns
Peak Reverse Recovery Current	I _{RM(REC)}			3.5	7	A
Reverse Recovery Charge	Q _{rr}			0.13	0.30	μC

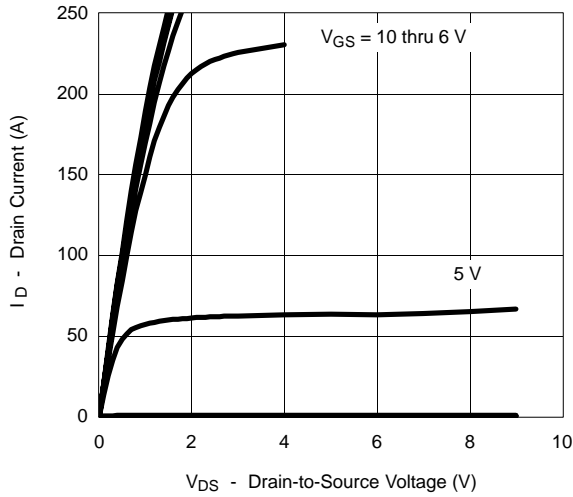
Notes

- Pulse test; pulse width ≤ 300 μs, duty cycle ≤ 2%.
- Guaranteed by design, not subject to production testing.
- Independent of operating temperature.

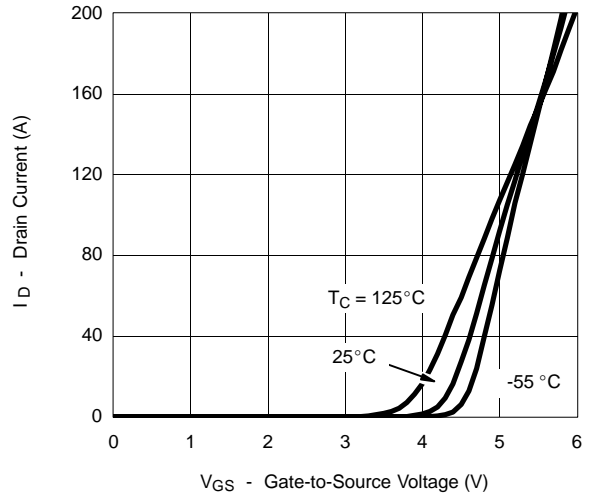


TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)

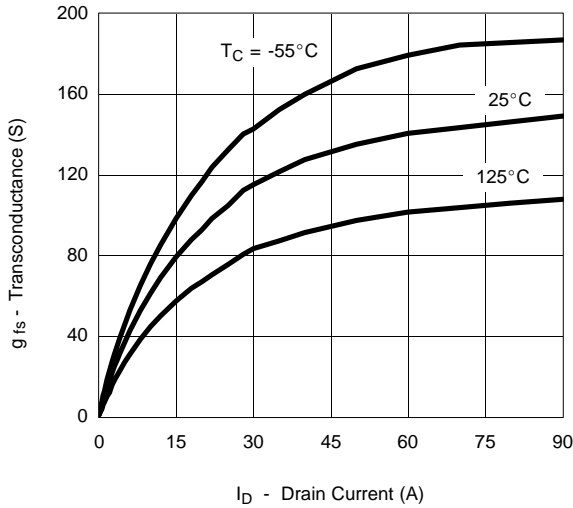
Output Characteristics



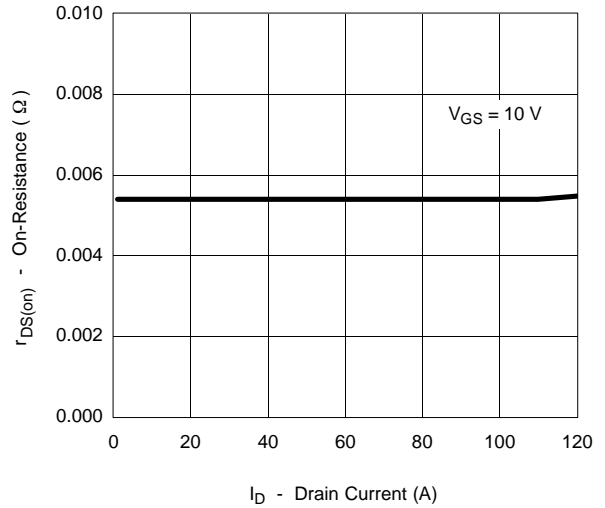
Transfer Characteristics



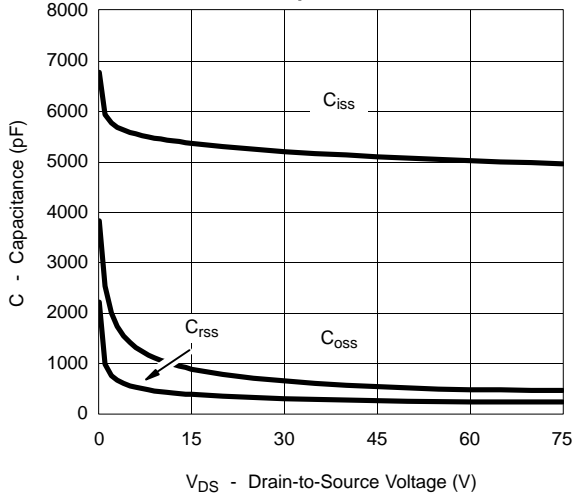
Transconductance



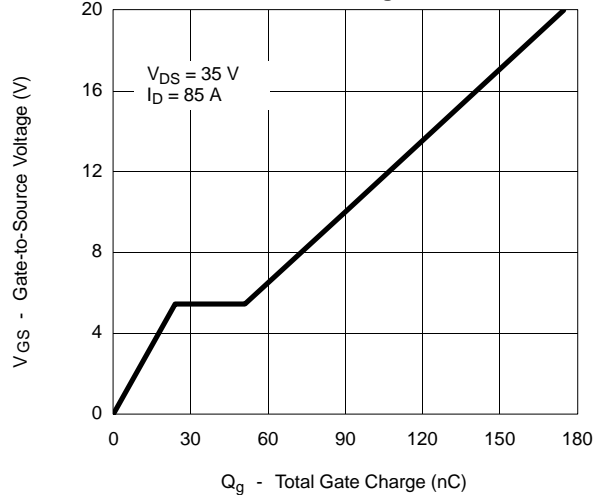
On-Resistance vs. Drain Current



Capacitance

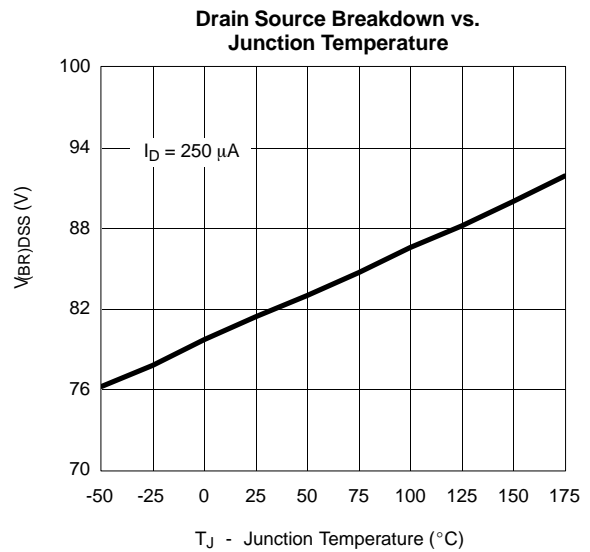
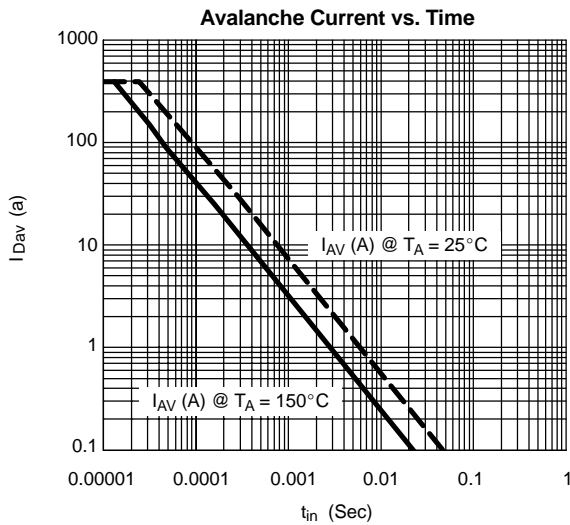
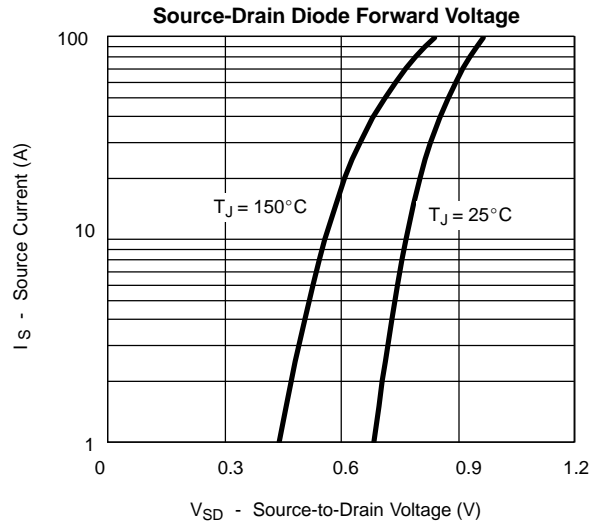
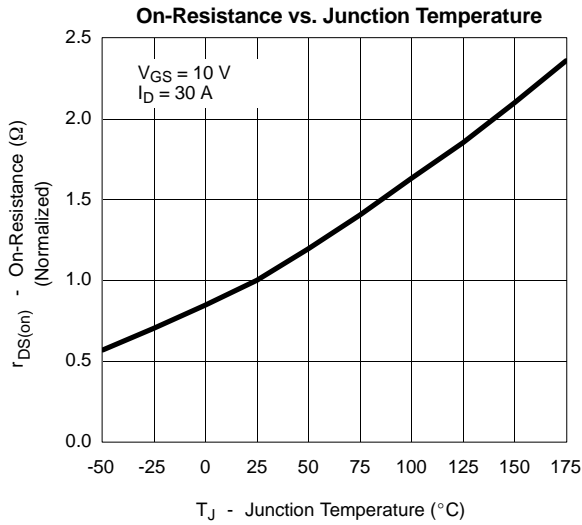


Gate Charge





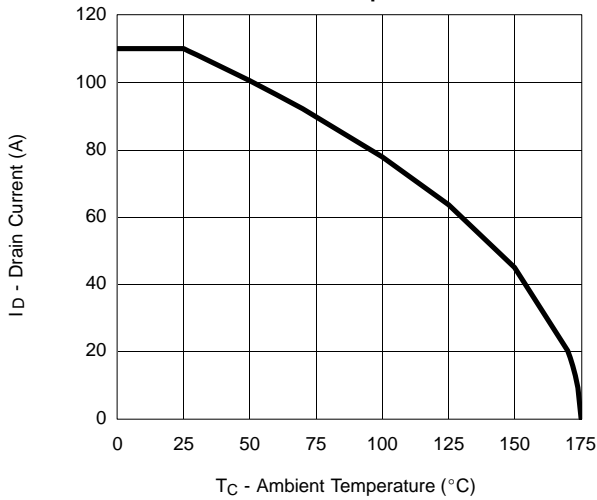
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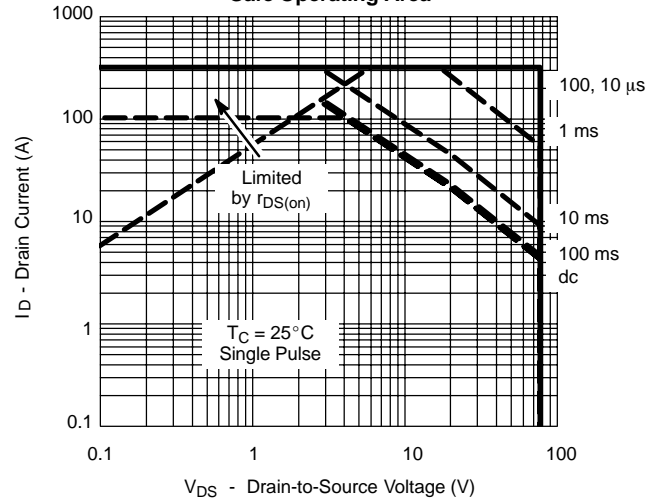


THERMAL RATINGS

Maximum Avalanche and Drain Current vs. Case Temperature



Safe Operating Area



Normalized Thermal Transient Impedance, Junction-to-Case

